# 'anasonic





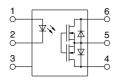
### Normally closed type with reinforced insulation

## Photo MOS® GE 1 Form B (AQV41OEH)



(Height includes standoff)

mm inch

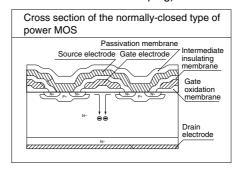


**RoHS** compliant

#### **FEATURES**

- 1.1 Form B output type
- 2. 60V type couples high capacity (0.55A) with low on-resistance (Typ. 1Ω).
- 3. Low on-resistance

This has been realized thanks to the built-in MOSFET processed by our proprietary method, DSD (Doublediffused and Selective Doping) method.



4. Controls low-level analog signals PhotoMOS feature extremely low closedcircuit offset voltage to enable control of low-level analog signals without distortion.

#### 5. High sensitivity and low onresistance

Can control max. 0.55 A load current with 5 mA input current.

Low on-resistance of Typ.  $1\Omega$ (AQV412EH).

6. Low-level off-state leakage current

7. Reinforced insulation: 5,000 V More than 0.4 mm internal insulation distance between inputs and outputs. Conforms to EN41003, EN60950 (reinforced insulation).

#### TYPICAL APPLICATIONS

- Power supply
- Measuring equipment
- Security equipment
- Telephone equipment
- · Sensing equipment

#### **TYPES**

	I/O isolation voltage	Output rating*		Doolsono	Part No.				Packing quantity	
					Through hole terminal Surface-mount terminal					
		Load Load voltage current	Lood	Package	,		Tape and reel packing style		Tube	Tape and reel
				Tube packing style		Picked from the 1/2/3-pin side	Picked from the 4/5/6-pin side			
	5,000 Vrms (Reinforced)	60 V	550 mA	4	AQV412EH	AQV412EHA	AQV412EHAX	AQV412EHAZ	1 tube contains:	
AC/DC dual use		1 350 V   130 mA   DIP6-nin	AQV410EH	AQV410EHA	AQV410EHAX	AQV410EHAZ	50 pcs. 1 batch contains:	1,000 pcs.		
		400 V	120 mA		AQV414EH	AQV414EHA	AQV414EHAX	AQV414EHAZ	500 pcs.	

-1-

Note: The surface mount terminal shape indicator "A" and the packing style indicator "X" or "Z" are not marked on the device.

<sup>\*</sup>Indicate the peak AC and DC values.

#### **RATING**

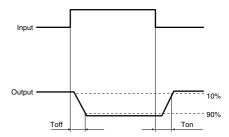
#### 1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

Item		Symbol	Type of connection	AQV412EH(A)	AQV410EH(A)	AQV414EH(A)	Remarks
	LED forward current	lF		50 mA			
Input	LED reverse voltage	VR			5 V		
	Peak forward current	IFP			1 A	f = 100 Hz, Duty factor = 0.1%	
	Power dissipation	Pin		75 mW			
	Load voltage (peak AC)	VL		60 V	350 V	400 V	
	Continuous load		Α	0.55 A	0.13 A	0.12 A	
Output		Iι	В	0.65 A	0.15 A	0.13 A	A connection: Peak AC, DC B.C connection: DC
	Current		С	0.8 A	0.17 A	0.15 A	B,O connection. BO
	Peak load current	I <sub>peak</sub>		1.5 A	0.4 A	0.3 A	A connection: 100 ms (1 shot), V <sub>L</sub> = DC
	Power dissipation	Pout			500 mW		
Total power dissipation		Р⊤			550 mW		
I/O isolation voltage		Viso			5,000 Vrms		
Ambient	Operating	Topr		-40	0 to +85°C -40 to +18	(Non-icing at low temperatures)	
temperature	Storage	T <sub>stg</sub>		-40	to +100°C -40 to +21		

#### 2. Electrical characteristics (Ambient temperature: 25°C 77°F)

Item				Type of connection	AQV412EH(A)	AQV410EH(A)	AQV414EH(A)	Condition
Input	LED operate (OFF) current	Typical Maximum	- I <sub>Foff</sub> —			IL= Max.		
	LED reverse (ON) current	Minimum	Fon			IL = Max.		
	LED reverse (ON) current	Typical	IFon					
	LED dropout voltage	Typical	VF	_	1.3	I <sub>F</sub> = 50 mA		
	LLD dropout voitage	Maximum	VF		1.5 V			
	On resistance	Typical	Ron	A	1 Ω	18 Ω	25.2 Ω	IF = 0 mA IL = Max. Within 1 s IF = 0 mA IL = Max. Within 1 s
		Maximum			2.5 Ω	35 Ω	50 Ω	
		Typical	- Ron	В	0.55 Ω	13 Ω	19 Ω	
Output		Maximum			1.3 Ω	17.5 Ω	25 Ω	
		Typical	Ron	С	0.3 Ω	6.5 Ω	10 Ω	IF = 0 mA IL = Max. Within 1 s
		Maximum			0.7 Ω	8.8 Ω	12.5 Ω	
	Off state leakage current	Maximum	ILeak	_	10 μΑ		$I_F = 5 \text{ mA}$ $V_L = \text{Max}.$	
Transfer characteristics	Operate (OFF) time*	Typical	Toff	_	3 ms	1.5 ms	1.3 ms	I <sub>F</sub> = 0 mA → 5 mA
	Operate (Or 1 ) time	Maximum	I OTT		8 ms	3.0	I∟ = Max.	
	Reverse (ON) time*	Typical	Ton	_	0.3 ms			I <sub>F</sub> = 5 mA $\rightarrow$ 0 mA I <sub>L</sub> = Max.
	11040100 (014) 11110	Maximum	1011		1.5 ms			
	I/O capacitance Typical Maximum		Ciso	_	0.8 pF 1.5 pF			f = 1 MHz V <sub>B</sub> = 0 V
	Initial I/O isolation resistance	Minimum	Riso	_	1,000 ΜΩ			500 V DC

#### \*Operate/Reverse time



#### 3. Recommended operating conditions (Ambient temperature: 25°C 77°F)

Please use under recommended operating conditions to obtain expected characteristics.

	Item	Symbol	Min.	Max.	Unit
	LED current	lF	I <sub>F</sub> 5		mA
AQV412EH(A)	Load voltage (Peak AC)	VL	_	48	V
	Continuous load current (A connection)	lı.	_	0.55	Α
AQV410EH(A)	Load voltage (Peak AC)	VL	_	280	V
	Continuous load current (A connection)	lı.	_	0.13	Α
AQV414EH(A)	Load voltage (Peak AC)	VL	_	320	V
	Continuous load current (A connection)	lı.	_	0.12	Α

#### ■ These products are not designed for automotive use.

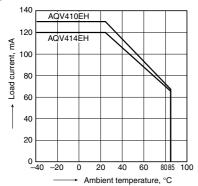
If you are considering to use these products for automotive applications, please contact your local Panasonic Corporation technical representative.

### **REFERENCE DATA**

1-(1). Load current vs. ambient temperature characteristics

Allowable ambient temperature: -40 to +85°C

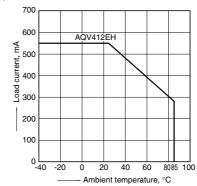
Type of connection: A



1-(2). Load current vs. ambient temperature characteristics

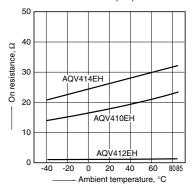
Allowable ambient temperature: -40 to +85°C

Type of connection: A



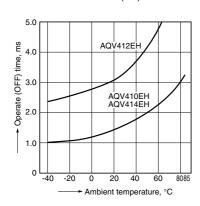
2. On resistance vs. ambient temperature characteristics

Measured portion: between terminals 4 and 6; LED current: 0 mA; Load voltage: Max. (DC); Continuous load current: Max. (DC)



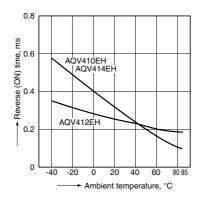
3. Operate (OFF) time vs. ambient temperature characteristics

LED current: 5mA; Load voltage: Max. (DC); Continuous load current: Max. (DC)



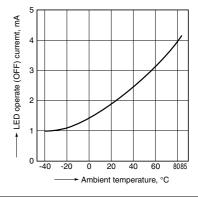
4. Reverse (ON) time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: Max. (DC); Continuous load current: Max. (DC)



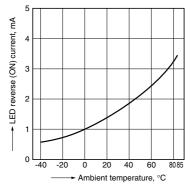
5. LED operate (OFF) current vs. ambient temperature characteristics

Sample: All types; Load voltage: Max. (DC); Continuous load current: Max. (DC)

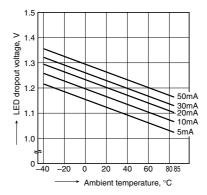


6. LED reverse (ON) current vs. ambient temperature characteristics

Sample: All types; Load voltage: Max. (DC); Continuous load current: Max. (DC)

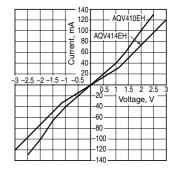


7. LED dropout voltage vs. ambient temperature characteristics Sample: All types; LED current: 5 to 50 mA



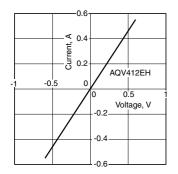
8-(1). Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 4 and 6; Ambient temperature:  $25^{\circ}C$   $77^{\circ}F$ 



8-(2). Current vs. voltage characteristics of output at MOS portion

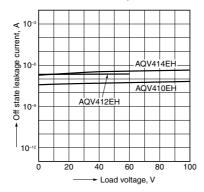
Measured portion: between terminals 4 and 6; Ambient temperature: 25°C 77°F



9. Off state leakage current vs. load voltage characteristics

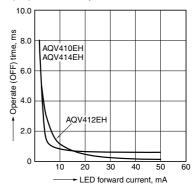
Sample: All types;

Measured portion: between terminals 4 and 6; LED current: 5 mA; Ambient temperature: 25°C 77°F



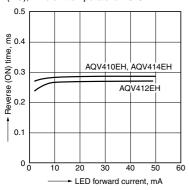
10. Operate (OFF) time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6; Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



11. Reverse (ON) time vs. LED forward current characteristics

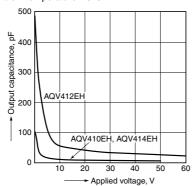
Measured portion: between terminals 4 and 6; Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



12. Output capacitance vs. applied voltage characteristics

Measured portion: between terminals 4 and 6; Frequency: 1 MHz;

Ambient temperature: 25°C 77°F



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